

PSMN1R2-30YLC

N-channel 30 V 1.25m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 3 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

	_				_		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$25 \text{ °C} \le T_j \le 175 \text{ °C}$		-	-	30	V
I _D	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	215	W
T _j	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12		-	1.35	1.65	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12		-	1.05	1.25	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure 14}}{\text{Figure 15}};$	-	11.6	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see $\frac{\text{Figure } 15}{\text{Figure } 15}$	-	38	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PSMN1R2-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN1R2-30YLC	1C230L

^{[1] % =} placeholder for manufacturing site code

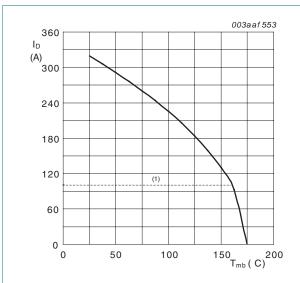
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

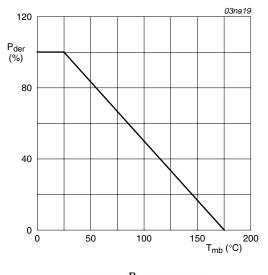
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4		-	1237	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	215	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		900	-	V
Source-drain	diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1237	Α
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; see Figure 3		-	209	mJ

^[1] Continuous current is limited by package.



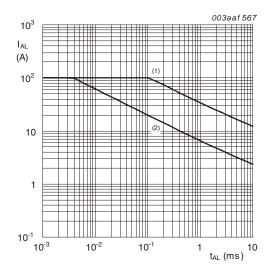
 $V_{GS} \ge 10V$; (1) Capped at 100A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



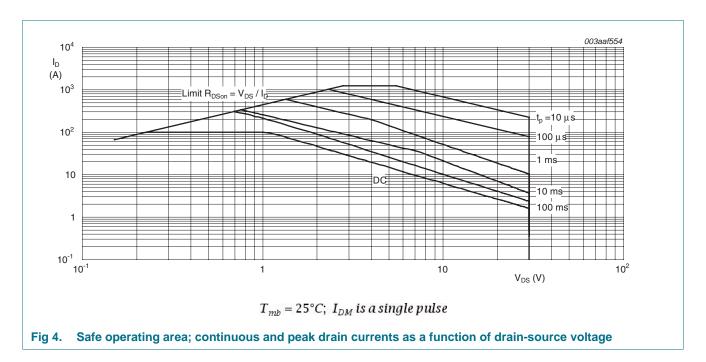
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j (init)} = 25 \,^{\circ}C$; (2) $T_{j (init)} = 100 \,^{\circ}C$ Single pulse avalanche rating; avalanche current as a function of avalanche time

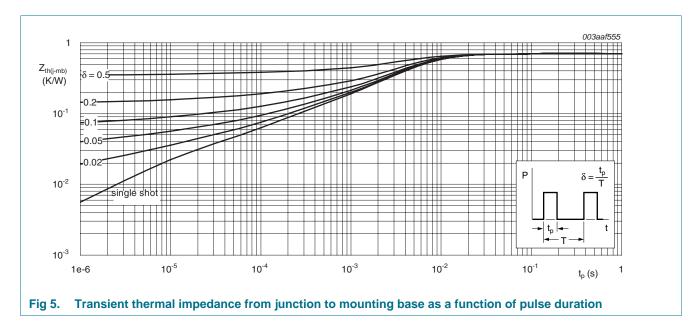
Fig 3.



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.58	0.7	K/W



7. Characteristics

Table 7. Characteristics

D	On white and		_		
Parameter	Conditions	Min	Тур	Max	Unit
			-	-	V
_					V
gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.46	1.95	V
	$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
	$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	1.35	1.65	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 13; see Figure 12	-	-	2.8	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	1.05	1.25	mΩ
	V_{GS} = 10 V; I_D = 25 A; T_j = 150 °C; see Figure 13; see Figure 12	-	-	2.05	mΩ
gate resistance	f = 1 MHz	-	1.1	2.2	Ω
characteristics					
total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	78	-	nC
	I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	38	-	nC
	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	75	-	nC
gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	10.3	-	nC
pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.7	-	nC
post-threshold gate-source charge		-	3.6	-	nC
gate-drain charge		-	11.6	-	nC
gate-source plateau voltage	I_D = 25 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.34	-	V
input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	5093	-	pF
output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	977	-	pF
reverse transfer capacitance		-	333	-	pF
turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	36	-	ns
rise time	$R_{G(ext)} = 4.7 \Omega$	-	60	-	ns
HOC WITH					
turn-off delay time		-	75	-	ns
		-	75 39	-	ns ns
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance gate resistance characteristics total gate charge pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	drain-source breakdown voltage I_D = 250 μA; V_GS = 0 V; T_j = 25 °C 30 I_D = 250 μA; V_GS = 0 V; T_j = -55 °C 27 gate-source threshold voltage I_D = 1 mA; V_DS = V_GS; T_j = 25 °C; 1.05 I_D = 10 mA; V_DS = V_GS; T_j = 150 °C 0.5 I_D = 10 mA; V_DS = V_GS; T_j = 150 °C 0.5 I_D = 1 mA; V_DS = V_GS; T_j = 55 °C 0.5 I_D = 1 mA; V_DS = V_GS; T_j = 55 °C 0.5 I_D = 1 mA; V_DS = 0 V; T_j = 25 °C 0.5 V_DS = 30 V; V_GS = 0 V; T_j = 25 °C 0.5 Grain-source on-state resistance V_GS = 16 V; V_DS = 0 V; T_j = 25 °C 0.5 Grain-source on-state resistance V_GS = 4.5 V; I_D = 25 A; T_j = 25 °C 0.5 V_GS = -16 V; V_DS = 0 V; T_j = 25 °C 0.5 V_GS = 10 V; I_D = 25 A; T_j = 150 °C; 0.5 V_GS = 10 V; I_D = 25 A; T_j = 150 °C; 0.5 See Figure 12 V_GS = 10 V; I_D = 25 A; T_j = 150 °C; 0.5 See Figure 13 see Figure 12 0.5 (C) 0.5 V_GS = 10 V; I_D = 25 A; T_j = 150 °C; 0.5 See Figure 14 see Figure 15 0.5 (C) 0.5 V_GS = 10 V; I_D = 25 A; T_J = 150 °C; 0.5 See Figure 14 see Figure 15 0.5 (C) 0.5 V_GS = 10 V; I_D = 25 A; V_DS = 15 V; V_GS = 10 V; 0.5 See Figure 14 see Figure 15 0.5 (C) 0.5 V_GS = 10 V; I_D = 25 A; V_DS = 15 V; V_GS = 4.5 V; 0.5 V_GS = 10 V; I_D = 25 A; V_DS = 15 V; V_GS = 4.5 V; 0.5 V_GS = 10 V; I_D = 25 A; V_DS = 15 V; V_GS = 4.5 V; 0.5 V_GS = 10 V; I_D = 25 A; V_DS = 15 V; V_GS = 4.5 V; 0.5 V_GS = 10 V; I_D = 25 A; V_DS = 15 V; V_GS = 4.5 V; 0.5 V_GS = 15 V; V_GS = 0 V; V_GS = 15 V; V_GS = 4.5 V; 0.5 V_GS = 15 V; V_GS = 0 V; I_S = 15 V; V_GS = 4.5 V; 0.5 V_GS = 15 V; V_GS = 0 V; I_S = 15 V; I_S = 0 V;	racteristics drain-source breakdown voltage I _D = 250 μA; V _{GS} = 0 V; T _J = 25 °C 30 - I _D = 250 μA; V _{GS} = 0 V; T _J = .55 °C 27 - I _D = 250 μA; V _{GS} = 0 V; T _J = .55 °C 27 - I _D = 250 μA; V _{GS} = 0 V; T _J = .55 °C 27 - I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25 °C; 1.05 1.46	$ \begin{array}{c} \text{racteristics} \\ \\ \text{drain-source} \\ \text{breakdown voltage} \\ \\ \text{lp} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \\ \text{lp} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 55 \ ^{\circ}\text{C} \\ \\ \text{gate-source threshold} \\ \text{voltage} \\ \\ \\ \text{voltage} \\ \\ \\ \text{lp} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \text{see Figure 10}; \text{see Figure 11} \\ \\ \text{lp} = 10 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 150 \ ^{\circ}\text{C} \\ \text{lp} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 55 \ ^{\circ}\text{C} \\ \text{lp} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 55 \ ^{\circ}\text{C} \\ \text{lp} = 1 \ \text{mA}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{lp} = 1 \ \text{mA}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{lp} = 1 \ \text{lp} = 10 \ \text{mA}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{lp} = 1 \ \text{lp} = 10 \ \ \text{lp} =$

 Table 7.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	33	-	nC
Source-drain	Source-drain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 17</u>	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	41.5	-	ns
Q _r	recovered charge	V _{DS} = 15 V	-	45	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 15 \text{ V; see } \frac{\text{Figure } 18}{\text{Figure } 18}$	-	25	-	ns
t _b	reverse recovery fall time		-	16.5	-	ns

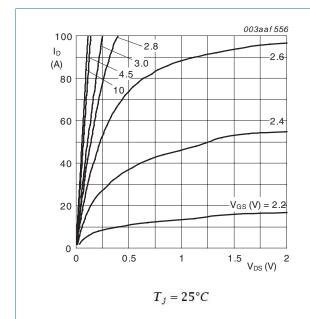
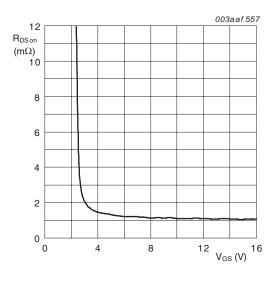


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

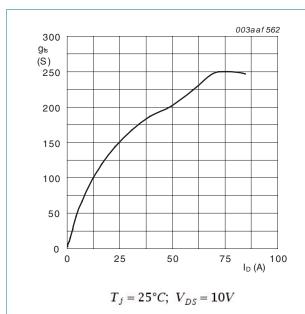


Fig 8. Forward transconductance as a function of drain current; typical values

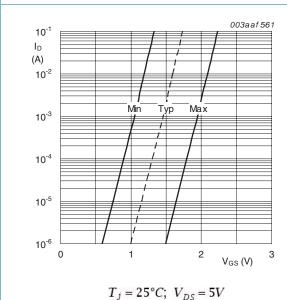
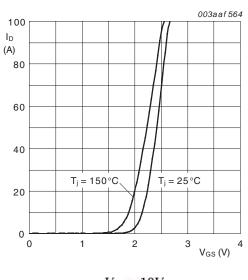


Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage

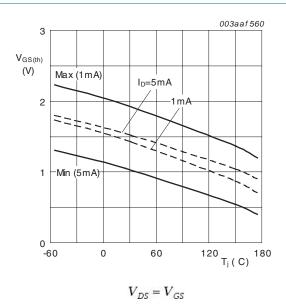


Fig 11. Gate-source threshold voltage as a function of junction temperature

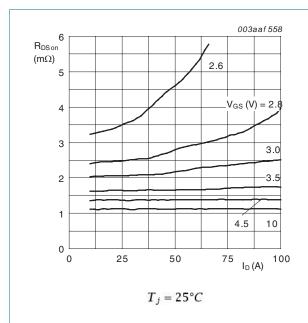


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

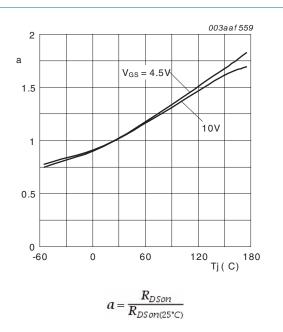


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

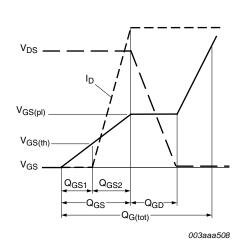


Fig 14. Gate charge waveform definitions

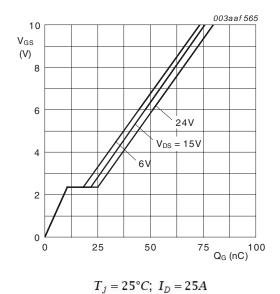


Fig 15. Gate-source voltage as a function of gate

charge; typical values

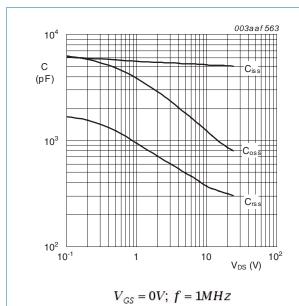


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

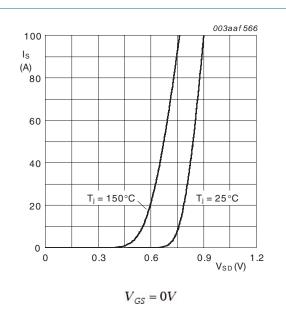


Fig 17. Source current as a function of drain-source voltage; typical values

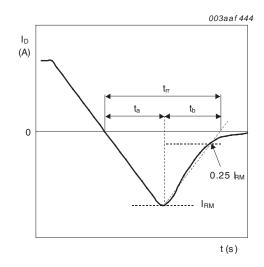


Fig 18. Reverse recovery timing definition

8. Package outline

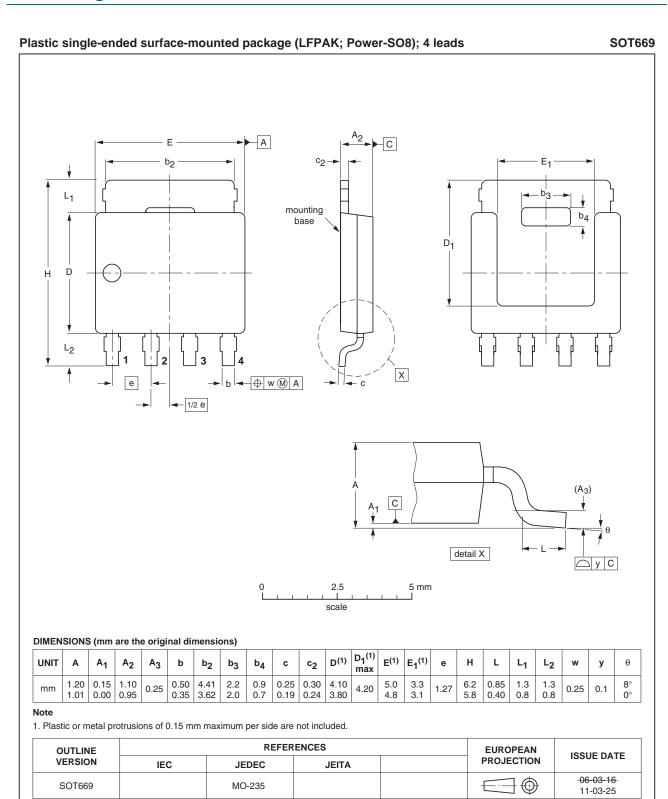


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN1R2-30YLC

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R2-30YLC v.1	20110503	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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PSMN1R2-30YLC

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PSMN1R2-30YLC

N-channel 30 V 1.25mΩ logic level MOSFET in LFPAK using NextPower

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12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking
5	Limiting values3
6	Thermal characteristics5
7	Characteristics6
8	Package outline11
9	Revision history12
10	Legal information13
10.1	Data sheet status
10.2	Definitions13
10.3	Disclaimers
10.4	Trademarks14
11	Contact information 14

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